# UTC UNISONIC TECHNOLOGIES CO., LTD

# HE8051

### NPN SILICON TRANSISTOR

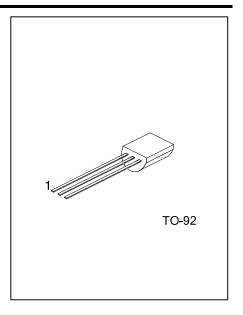
# LOW VOLTAGE HIGH CURRENT SMALL SIGNAL NPN **TRANSISTOR**

#### **DESCRIPTION**

The UTC HE8051 is a low voltage high current small signal NPN transistor, designed for Class B push-pull 2W audio amplifier for portable radio and general purpose applications.

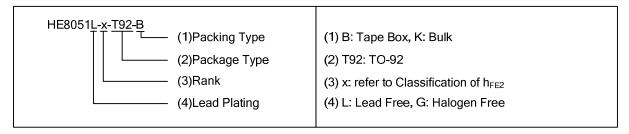
#### **FEATURES**

- \* Collector current up to 1.5A
- \* Collector-Emitter voltage up to 25 V
- \* complimentary to UTC HE8551

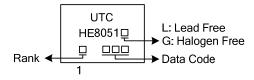


#### ORDERING INFORMATION

Order I	Number	Dookogo	Pin Assignment			Dooking
Lead Free	Halogen Free	Package	1	2	3	Packing
HE8051L-x-T92-B	HE8051G-x-T92-B	TO-92	Е	В	С	Tape Box
HE8051L-x-T92-K	HE8051G-x-T92-K	TO-92	Е	В	С	Bulk



#### **MARKING**



www.unisonic.com.tw

#### ■ ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	$V_{CBO}$	40	V
Collector-Emitter Voltage	$V_{CEO}$	25	V
Emitter-Base Voltage	$V_{EBO}$	6	V
Collector Dissipation (T <sub>A</sub> =25°C)	Pc	1	W
Collector Current	Ic	1.5	Α
Junction Temperature	$T_J$	+150	°C
Storage Temperature	T <sub>STG</sub>	-40 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

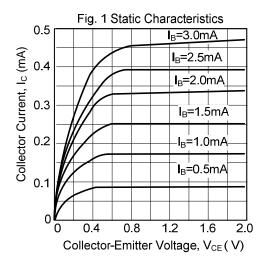
## ■ ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C, unless otherwise specified)

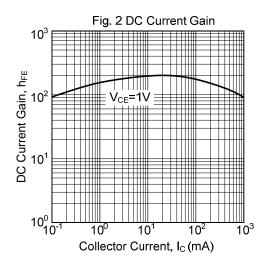
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	$BV_CBO$	$I_C=100\mu A,\ I_E=0$	40			V
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	I <sub>C</sub> =2mA, I <sub>B</sub> =0	25			V
Emitter-Base Breakdown Voltage	$BV_{EBO}$	I <sub>E</sub> =100μA, I <sub>C</sub> =0	6			V
Collector Cut-Off Current	I <sub>CBO</sub>	$V_{CB}=35V$ , $I_E=0$			100	nA
Emitter Cut-Off Current	I <sub>EBO</sub>	$V_{EB}=6V$ , $I_{C}=0$			100	nA
	h <sub>FE1</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =5mA	45	135		
DC Current Gain	h <sub>FE2</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =100mA	85	160	500	
	h <sub>FE3</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =800mA	40	110		
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	I <sub>C</sub> =800mA, I <sub>B</sub> =80mA			0.5	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	I <sub>C</sub> =800mA, I <sub>B</sub> =80mA			1.2	V
Base-Emitter Voltage	$V_{BE}$	V <sub>CE</sub> =1V, I <sub>C</sub> =10mA			1.0	V
Current Gain Bandwidth Product	f⊤	V <sub>CE</sub> =10V, I <sub>C</sub> =50mA	100			MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz		9.0		pF

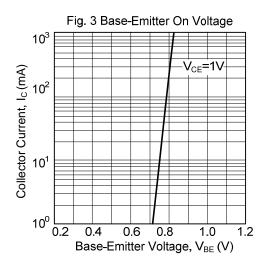
## ■ CLASSIFICATION OF h<sub>FE2</sub>

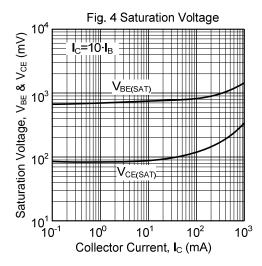
RANK	С	D	Е
RANGE	120-200	160-300	250-500

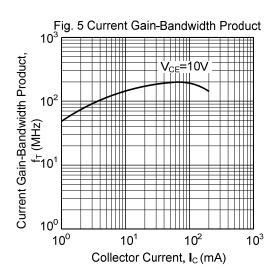
#### ■ TYPICAL CHARACTERISTICS

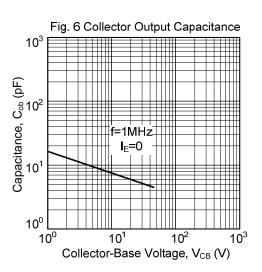












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